## X-ray absorption and emission studies of the electronic states of visible-light semiconductor photocatalyst: Rh-doped SrTiO<sub>3</sub>

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Rh-doped SrTiO<sub>3</sub> is a visible-light semiconductor photocatalyst, and the valence states of Rh are closely related to the reactivity of photocatalyst [1]. However, the electronic states of valence and conduction band have not been directly determined yet. In this study, we investigated both occupied and unoccupied states of Rh-doped SrTiO<sub>3</sub> samples as a function of Rh amount and the valence of Rh using X-ray emission spectroscopy (XES) and absorption spectroscopy (XAS) at BL07LSU in SPring8.

Rh:SrTiO<sub>3</sub> powders with Rh doping levels of 0, 1, 3, and 5 at% were prepared in the following way. Mixtures of SrCO<sub>3</sub> (baked at 300°C for 1 hour before use), TiO<sub>2</sub>, and Rh<sub>2</sub>O<sub>3</sub> were pre-calcined at 900°C for 5 hours, followed by heating at 1100°C for 10 hours. An excess amount of Sr (7 at%) was used in the starting materials. The powders were pressed into thin pellets at 10 MPa and calcined at 1200°C for 12 hours. This synthesis process produced samples with Rh<sup>4+</sup> substituting at the Ti<sup>4+</sup> site. Valence control of Rh was made by annealing a Rh<sup>4+</sup>:SrTiO<sub>3</sub> pellet in a H<sub>2</sub> atmosphere at 300°C for 2 hours, reducing Rh<sup>4+</sup> to Rh<sup>3+</sup>. A color difference between the Rh<sup>4+</sup> (purple) and Rh<sup>3+</sup> (yellow) samples are observed visually, as shown in Figure 1. Each sample was confirmed to be single phase by x-ray diffraction.

Figure 2 shows a series of O1s XAS spectra of Rh<sup>4+/3+</sup>:SrTiO<sub>3</sub> and non-doped SrTiO<sub>3</sub>. According to the dipole selection rules, the O1s XAS of Rh:SrTiO<sub>3</sub> corresponds to a transition from the O1s core level to an unoccupied O2p state that is hybridized with Ti3d or Rh4d states. The main peak at ~531 eV is composed mainly of Ti3d states hybridized with the O2pstates, forming the conduction band of SrTiO<sub>3</sub>. The spectral intensity in the gap region is shown on an expanded  $(\times 2)$ scale above each spectrum. The intensity of the unoccupied in-gap peak at ~1.5 eV below the CB minimum increased with increasing the Rh<sup>4+</sup>



Figure 1. Photos of prepared Rh:SrTiO<sub>3</sub> thin pellets



Figure 2. (a) O1s XAS spectra of Rh<sup>4+</sup>(x at%):SrTiO<sub>3</sub> (x = 0, 1, 3, 5) and Rh<sup>3+</sup> (5 at%):SrTiO<sub>3</sub>. (b) Energy level diagram for the transitions probed by O1s XAS.

doping level. Note that no absorption peak was observed in a 5 at%  $Rh^{3+}$ :SrTiO<sub>3</sub> sample. Thus, we assign the peak at 528.2 eV to a  $Rh^{4+}$  acceptor level, in accordance with the original interpretation of the UV-Vis-NIR absorption spectra [2,3].

Figure 3 shows a series of O1*s* XES spectra of  $Rh^{4+/3+}$ :SrTiO<sub>3</sub> and non-doped SrTiO<sub>3</sub>. samples with the excitation energy of 530.9 eV. The two main peaks at 523.5 and 526 eV are assigned to fluorescence related to transitions from bonding and non-bonding O2*p* states to the O1*s* core level, respectively [5]. The small peak located at 530.9 eV was an elastically scattered incident x-ray. A small but systematic emission increases in the VB shoulder region from 527 to 528.3 eV with increasing Rh content could be assigned to the Rh<sup>4+/3+</sup> donor levels. A spectral weight shift to higher emission energy by ~0.5 eV is evident for the reduced Rh<sup>3+</sup>:SrTiO<sub>3</sub> sample. Note that the Rh donor levels close to the VB maximum of SrTiO<sub>3</sub> were observed as a shoulder close to the band-gap excitation energy in the UV-Vis-NIR absorption spectra of the Rh<sup>4+/3+</sup>:SrTiO<sub>3</sub> samples [2,3].



Figure 3. (a) O1s XAS of Rh<sup>4+</sup>(x at%):SrTiO<sub>3</sub> (x = 0, 1, 3, 5), Rh<sup>3+</sup>(5 at%):SrTiO<sub>3</sub>, and non-doped SrTiO<sub>3</sub>, taken with the x-ray energy of 530.9 eV. The inset shows an expansion of the top of the valence band. (b) A schematic view of the transitions involved in O1s XES.

Based on the present XAS and XES results, the main difference in the photocatalytic activity between  $Rh^{4+}$ : and  $Rh^{3+}$ :SrTiO<sub>3</sub> can be explained by the difference in the in-gap Rh states. It is known that the photocatalytic activity of Rh:SrTiO<sub>3</sub> increases during the induction period, when  $Rh^{4+}$  is partially converted to  $Rh^{3+}$  [2]. We can conclude that the lower photocatalytic efficiency of  $Rh^{4+}$ :SrTiO<sub>3</sub> is related to the appearance of the unoccupied mid-gap state that may serve as a recombination center for the photoexcited carriers.

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## References

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